

N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88 6 April 2021 Product d

**Product data sheet** 

### 1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a copper-clip LFPAK88 package. This product has been fully designed and qualified to meet beyond AEC-Q101 requirements delivering high performance and reliability.

### 2. Features and benefits

- Fully automotive qualified to beyond AEC-Q101:
- -55 °C to +175 °C rating suitable for thermally demanding environments
- LFPAK88 package:
  - Designed for smaller footprint and improved power density over older wire bond packages such as D<sup>2</sup>PAK for today's space constrained high power automotive applications
  - Thin package and copper clip enables LFPAK88 to be highly efficient thermally
- LFPAK copper clip technology enabling improvements over wire bond packages by:
  - Increased maximum current capability and excellent current spreading
  - Improved R<sub>DSon</sub>
  - Low source inductance
  - Low thermal resistance R<sub>th</sub>
- LFPAK Gull Wing leads:
  - Flexible leads enabling high Board Level Reliability absorbing mechanical and thermal cycling stress, unlike traditional QFN packages
  - · Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joint
- Unique 40 V Trench 9 superjunction technology:
  - Reduced cell pitch and superjunction platform enables lower R<sub>DSon</sub> in the same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight V<sub>GS(th)</sub> limits enable easy paralleling of MOSFETs

### 3. Applications

- 12 V automotive systems
- 48 V DC/DC systems (on 12 V secondary side)
- Higher power motors, lamps and solenoid control
- Reverse polarity protection
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Quick reference data								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	500	A	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	375	W	



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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11		0.33	0.47	0.55	mΩ
Dynamic ch	naracteristics			•			
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; Fig. 13; Fig. 14		-	32	65	nC
Source-drai	in diode						
Qr	recovered charge	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ [2]	[2]	-	93	-	nC
S	softness factor	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C		-	0.83	-	

[1] 500A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] includes capacitive recovery

### 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	S	source	0	G-UFA
4	S	source		mbb076 S
mb	D	mounting base; connected to drain	LFPAK88 (SOT1235)	

### 6. Ordering information

Type number	Package	Package					
	Name	Description	Version				
BUK7S0R5-40H	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235				

### 7. Marking

Table 4. Marking codes						
Type number	Marking code					
BUK7S0R5-40H	7S0R540H					

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	40	V

#### N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> = 175 °C		-10	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	375	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	500	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	2237	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode		-			_
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	500	А
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C		-	2237	А
Avalanche r	ruggedness	1				
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 120 \text{ A};  V_{sup} \leq \text{ 40 V};  \text{R}_{GS} = 50  \Omega; \\        $	[2] [3]	-	1375	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup}$ = 40 V; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; R <sub>GS</sub> = 50 Ω; <u>Fig. 4</u>	[4]	-	315	A

[1] 500A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.

[4] Protected by 100% test.

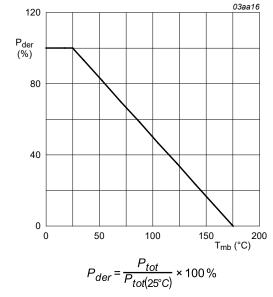
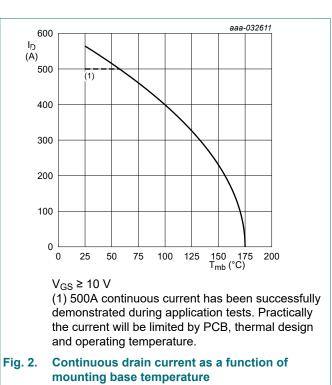
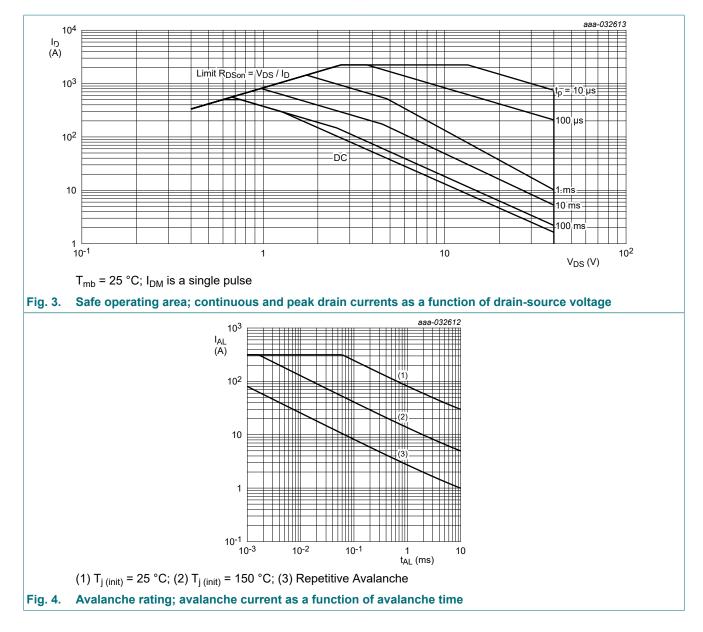


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



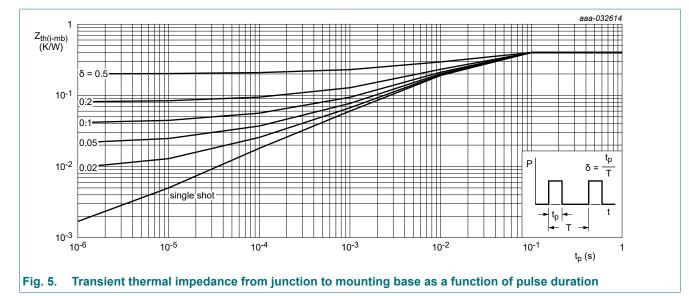


### 9. Thermal characteristics

### Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.35	0.4	K/W

#### N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88



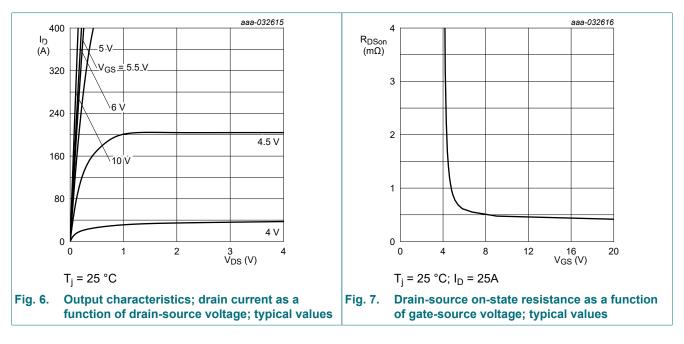
### **10. Characteristics**

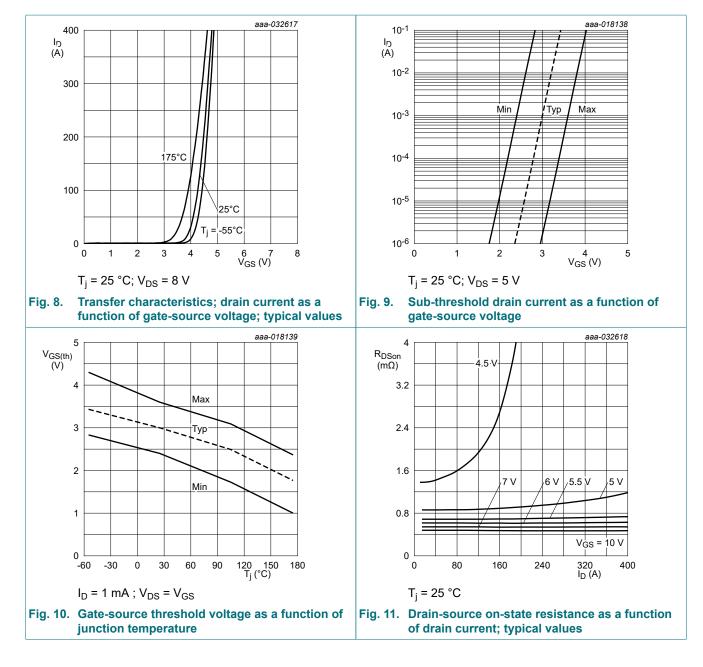
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics	· · ·				
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	43	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -40 °C	-	40.5	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	40	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.4	3	3.6	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <u>Fig. 10</u>	-	-	4.3	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <u>Fig. 10</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.2	2.9	μA
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	4.6	25	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	455	1000	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	0.33	0.47	0.55	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; Fig. 12	0.47	0.68	0.87	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 12	0.52	0.75	0.95	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12	0.65	0.93	1.19	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.37	0.92	2.31	Ω
Dynamic ch	aracteristics		I			
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	190	267	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	51	77	nC
Q <sub>GD</sub>	gate-drain charge		-	32	65	nC

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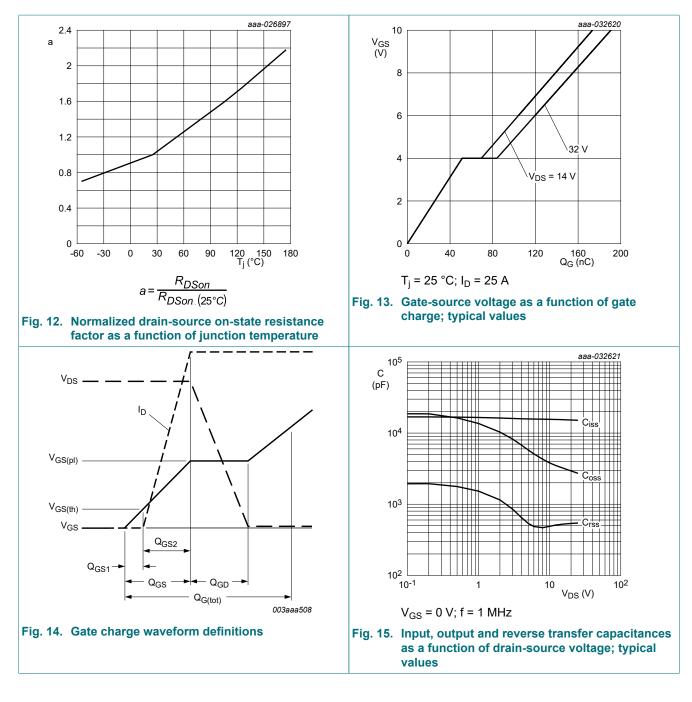
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		-	15116	21162	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	2718	3805	pF
C <sub>rss</sub>	reverse transfer capacitance	-		-	544	1197	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω		-	40	-	ns
t <sub>r</sub>	rise time			-	33	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	117	-	ns
t <sub>f</sub>	fall time			-	48	-	ns
Source-dra	ain diode					1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>		-	0.79	1	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$		-	62	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C	[1]	-	93	-	nC
S	softness factor			-	0.83	-	
		$I_{S}$ = 25 A; dI <sub>S</sub> /dt = -500 A/µs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C		-	0.73	-	

[1] includes capacitive recovery

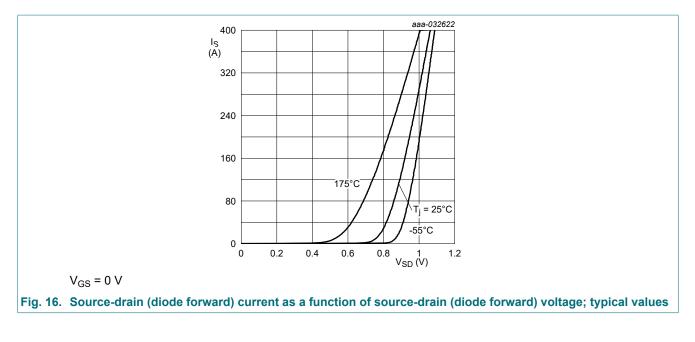




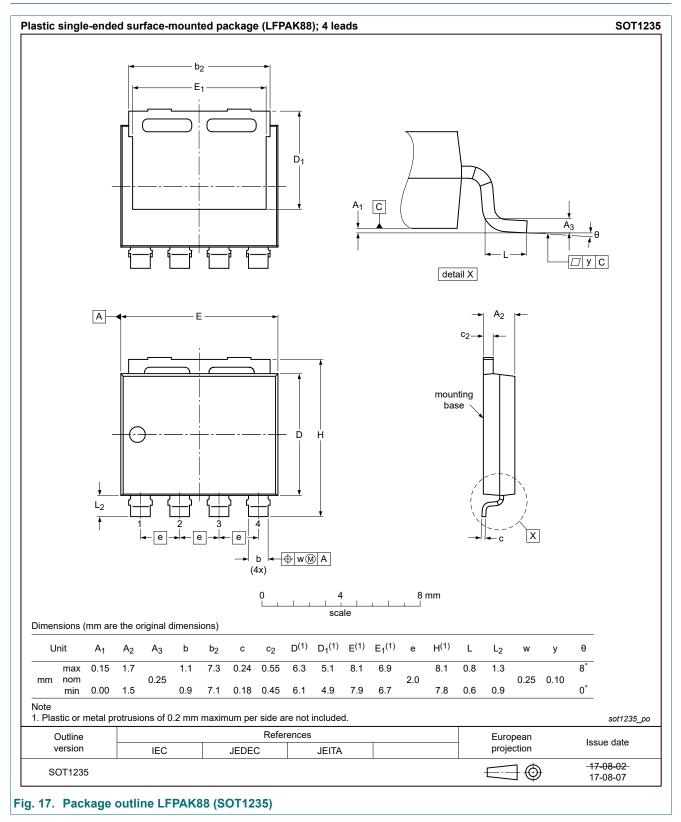
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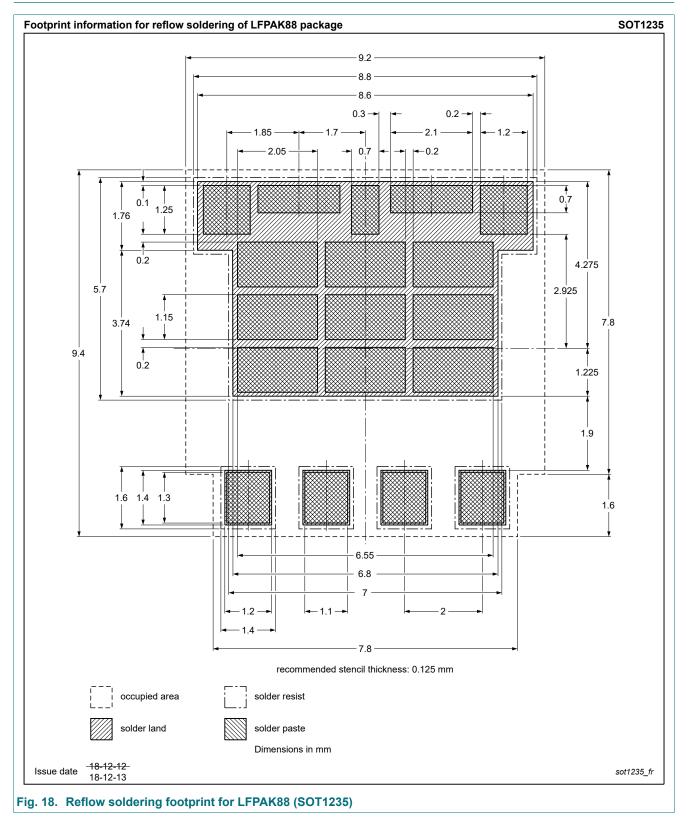
#### N-channel 40 V, 0.5 mOhm standard level MOSFET in LFPAK88



### 11. Package outline



# 12. Soldering



### 13. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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